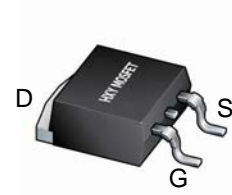




## Description

The IRFR3410PbF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

## General Features

$V_{DS} = 100V$   $I_D = 30A$

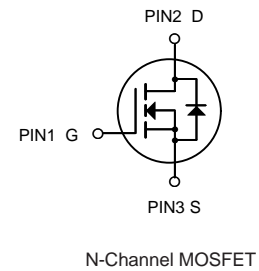
$R_{DS(ON)} < 48m\Omega$  @  $V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRFR3410PbF	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_c=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	30	A
$I_D@T_c=100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	13	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	80	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	30	mJ
$P_D@T_c=25^\circ C$	Total Power Dissipation <sup>4</sup>	42	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	3.6	$^\circ C/W$



### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.2	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	37	48	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	39	55	mΩ
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	-	1964	-	pF
C <sub>oss</sub>	Output Capacitance		-	90	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	74	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =80V, I <sub>D</sub> =20A, V <sub>GS</sub> =4.5V	-	20	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	3.1	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	14	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =80V, I <sub>D</sub> =20A, R <sub>G</sub> =3.1Ω, V <sub>GS</sub> =4.5V	-	11	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	91	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	40	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	71	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	27	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, dI/dt=100A/μs	-	64	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	152	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

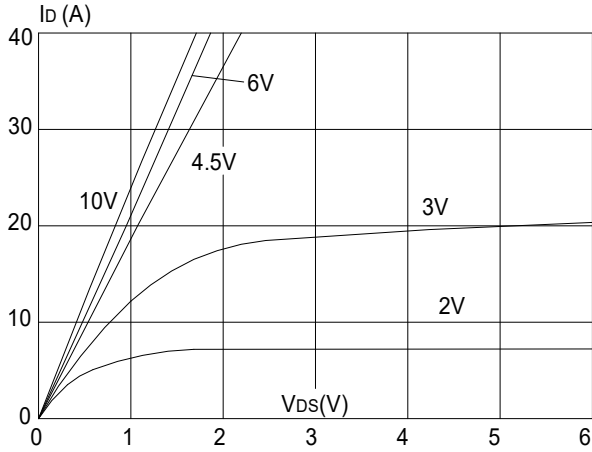
2. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω, I<sub>AS</sub>= 11A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

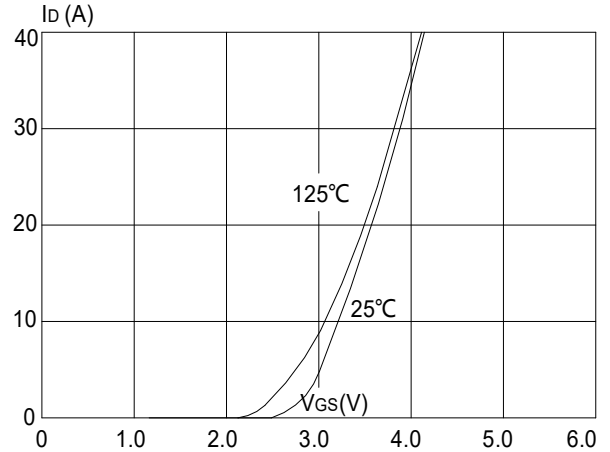


## Typical Performance Characteristics

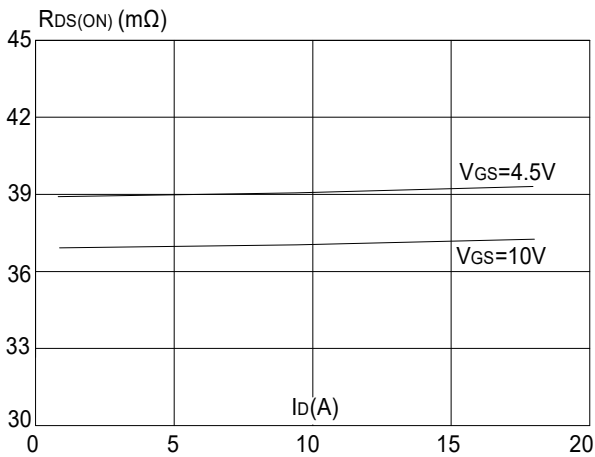
**Figure 1: Output Characteristics**



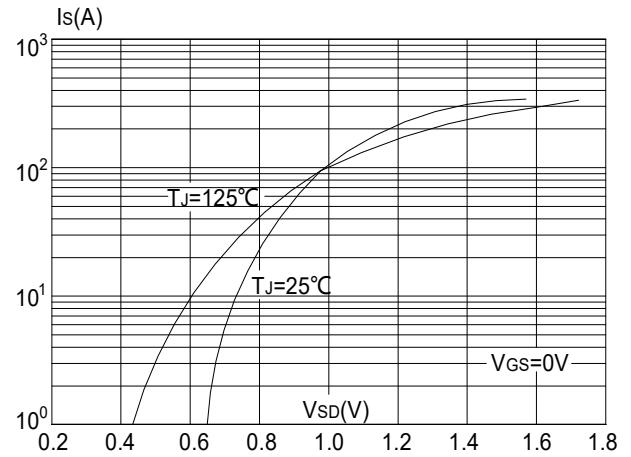
**Figure 2: Typical Transfer Characteristics**



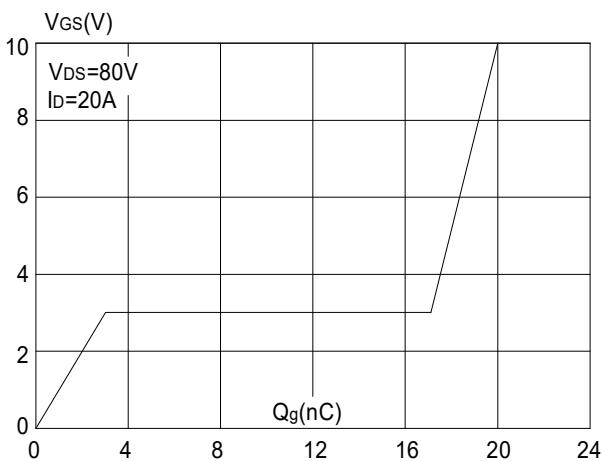
**Figure 3: On-resistance vs. Drain Current**



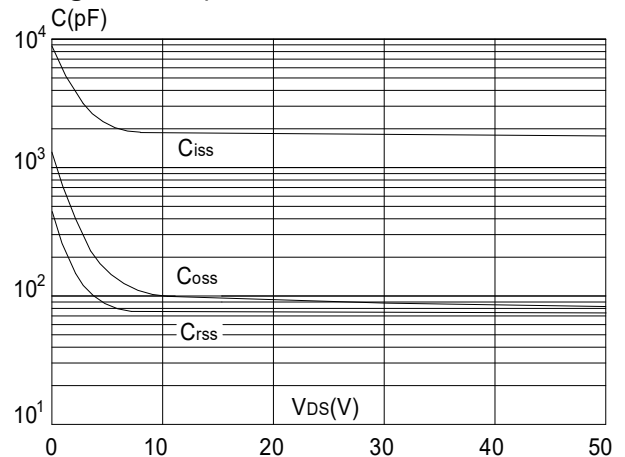
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

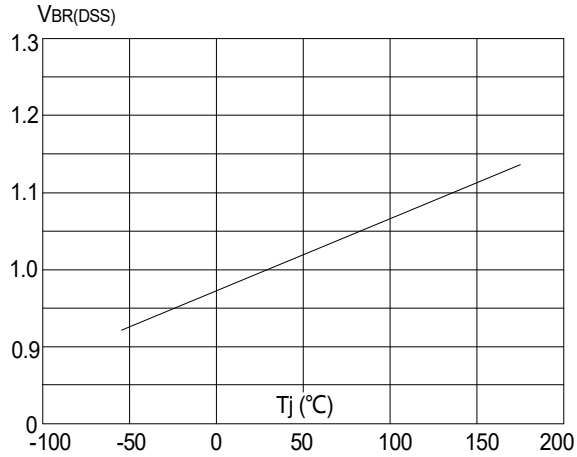


**Figure 6: Capacitance Characteristics**

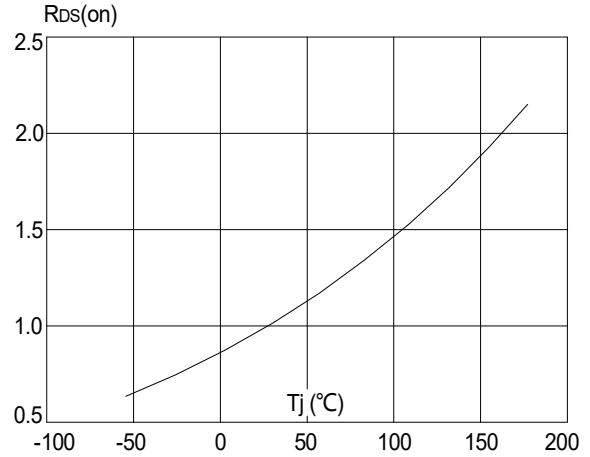




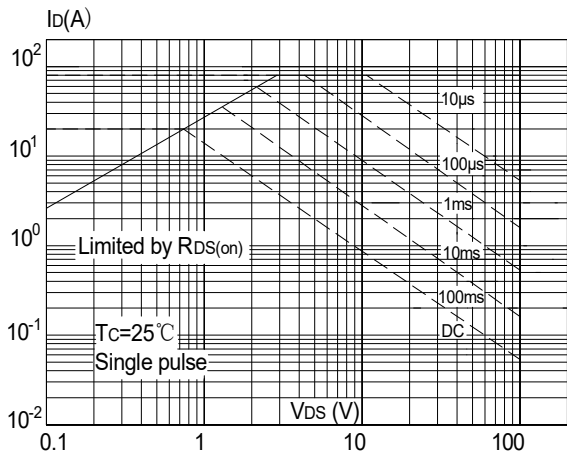
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



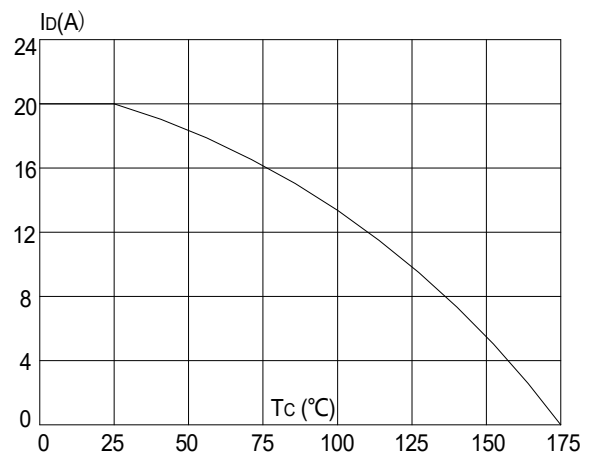
**Figure 8:** Normalized on Resistance vs. Junction Temperature



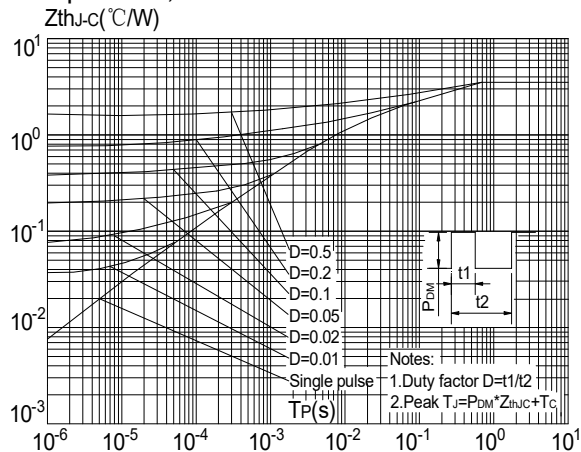
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case







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